



Data Sheet

November 2013

30 A, 1200 V, Hyperfast Diode

The RHRP30120 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling/ clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

OrderingInformation

PART NUMBER	PACKAGE	BRAND
RHRP30120	TO-220AC	RHR30120

NOTE: When ordering, use theentire part number

Symbol

Features

☑Hyperfast Recovery t_{rr} = 85 ns (@ # = 30 A)
☑Max Forward Voltage, ¥ = 3.2 V (@ T_c = 25☑C)
☑1200 V Reverse Voltage and High Reliability
☑Avalanche Energy Rated
☑RoHS Compliant

Application

Switching 'ow Supplies

☑ Power Switching Sircuits

a Kaging

JEDEC TO-220AC

ANODE CATHODE

CATHODE (FLANGE)

AbsoluteMaximumRatings T > -25 °C								
		RHRP30120	UNIT					
PeakRepetitiveReverseVoltageV	RRM	1200	V					
WorkingPeakReverseVoltageV	RWM	1200	V					
DCBlockingVoltageV	R	1200	V					
AverageRectifiedForwardCurrentI	F(AV)	30	Α					
$(T_C = 78 ^{\circ}C)$								
RepetitivePeakSurgeCurrent	FRM	60	Α					
(Square Wave, 20 kHz)								
NonrepetitivePeakSurgeCurrent	FSM	300	Α					
(Halfwave, 1 Phase, 60 Hz)								
MaximumPowerDissipationP	D	125	W					
AvalancheEnergy(SeeFigures7and8) E	AVL	30	mJ					
OperatingandStorageTemperature	STG_pT_J	-65 to 175	oC					

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ElectricalSpecifications T_C =25 °C, Unless Otherwise Specified

SYMBOL	TESTCONDITION	MIN	TYP	MAX	UNIT
V _F	I _F = 30 A	_	-	3.2	V
	I _F =30 A,T _C =150 °C	_	-	.@	V
I _R	V _R = 1200 V	_	-	250	ĽΑ
	$V_R = 1200 \text{ V}, T_C = 150 ^{\circ}\text{C}$	_	-	1	Am
t _{rr}	I _F =1 A, di _F /dt = 100 A/∞s	_	-	56	ns
	I _F =30 A,di _F /dt = 100 A/∞s	_	-	58	ns
ta	I _F =30 A,di _F /dt = 100 A/∞s	_	48	-	ß
t _b	I _F =30 A,di	_	2	-	В
RZJC		_	-	.2	C/W

DEFINITIONS

V_F =Instantaneousforwardvoltage(pw=300 ∞s,D=2%).

I_R =Instantaneousreversecurrent.

 T_{rr} = Reverse recovery time (See Figure 6), summation of $t_a + t_b$.

ta = Time to reach peak reverse current (See Figure 6).

Tf irpmo elengato placeted zero crossing of ham b

RUJC =Thermalresistancejunctiontocase.

pw=pulsewidth.

D=dutycycle.

TypicalPerformanceCurves

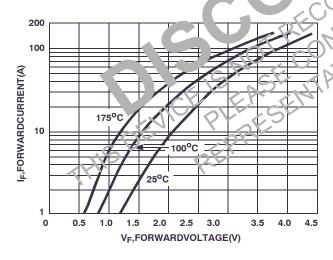


FIGURE1. FORWARDCURRENTvsFORWARDVOLTAGE

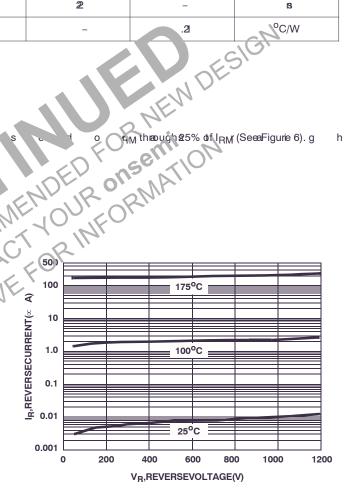


FIGURE2. REVERSECURRENTVSREVERSEVOLTAGE

TypicalPerformanceCurves (Continued)

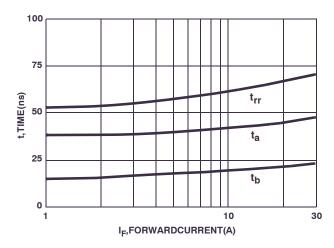
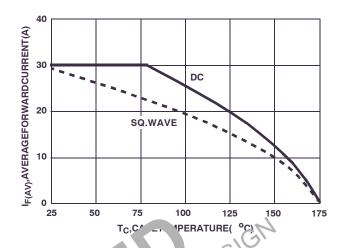
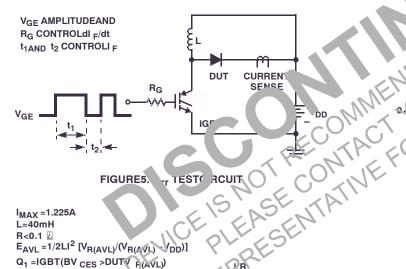


FIGURE3. t rpta ANDt b CURVESvsFORWARDCURRENT



FIGUE 4. CUL EN DERATINGCURVE

TestCircuitsandWaveforms



TEST ROUIT FIGURE5.

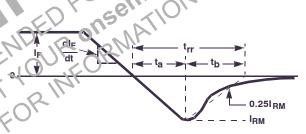


FIGURE6. trr WAVEFORMSANDDEFINITIONS

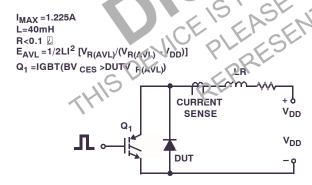


FIGURE7. AVALANCHEENERGYTESTCIRCUIT

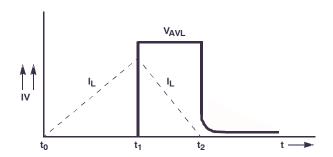


FIGURE8. AVALANCHECURRENTANDVOLTAGE **WAVEFORMS**



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